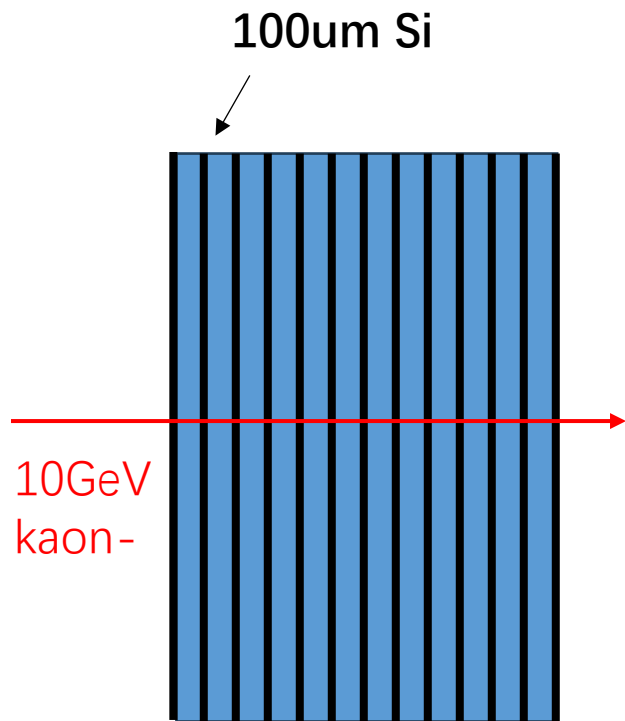


dE/dX measurement by silicon

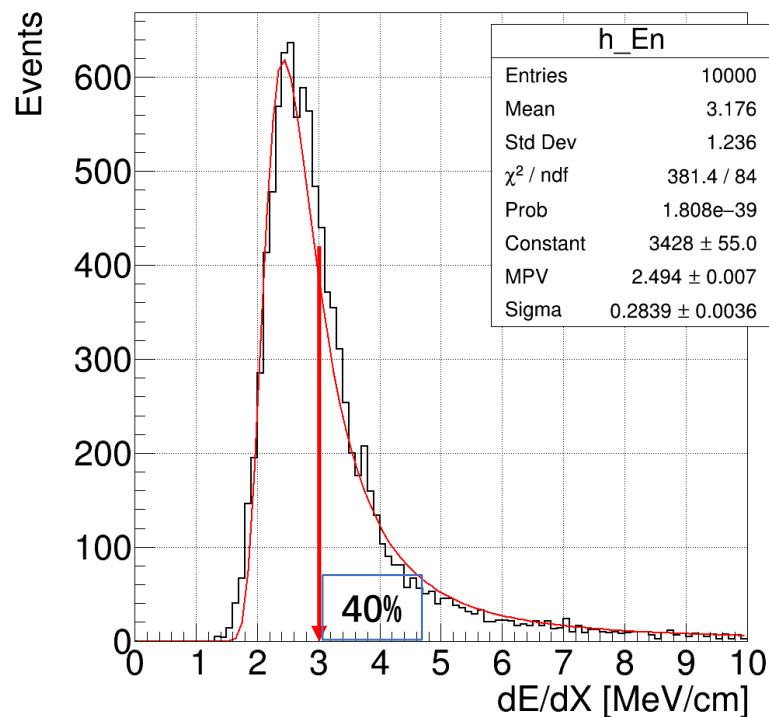
截断平均法测量多层si的dEdX (layers>20)

➤ 截断平均法测量dE/dX，截断点取能量的60%可以获得最佳dE/dX分辨。

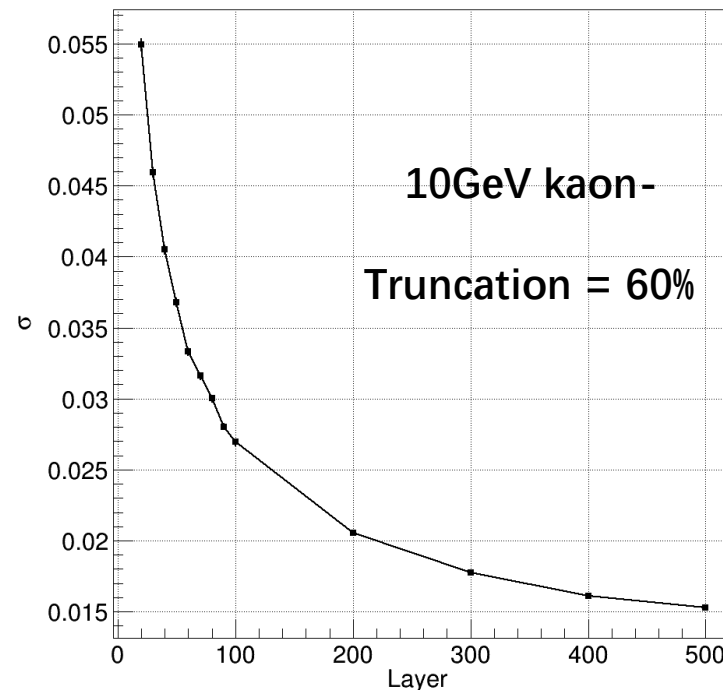


多层硅dEdx测量理想模型。
Si沉积能量为MCTruth Energy。

Si探测效率100%;

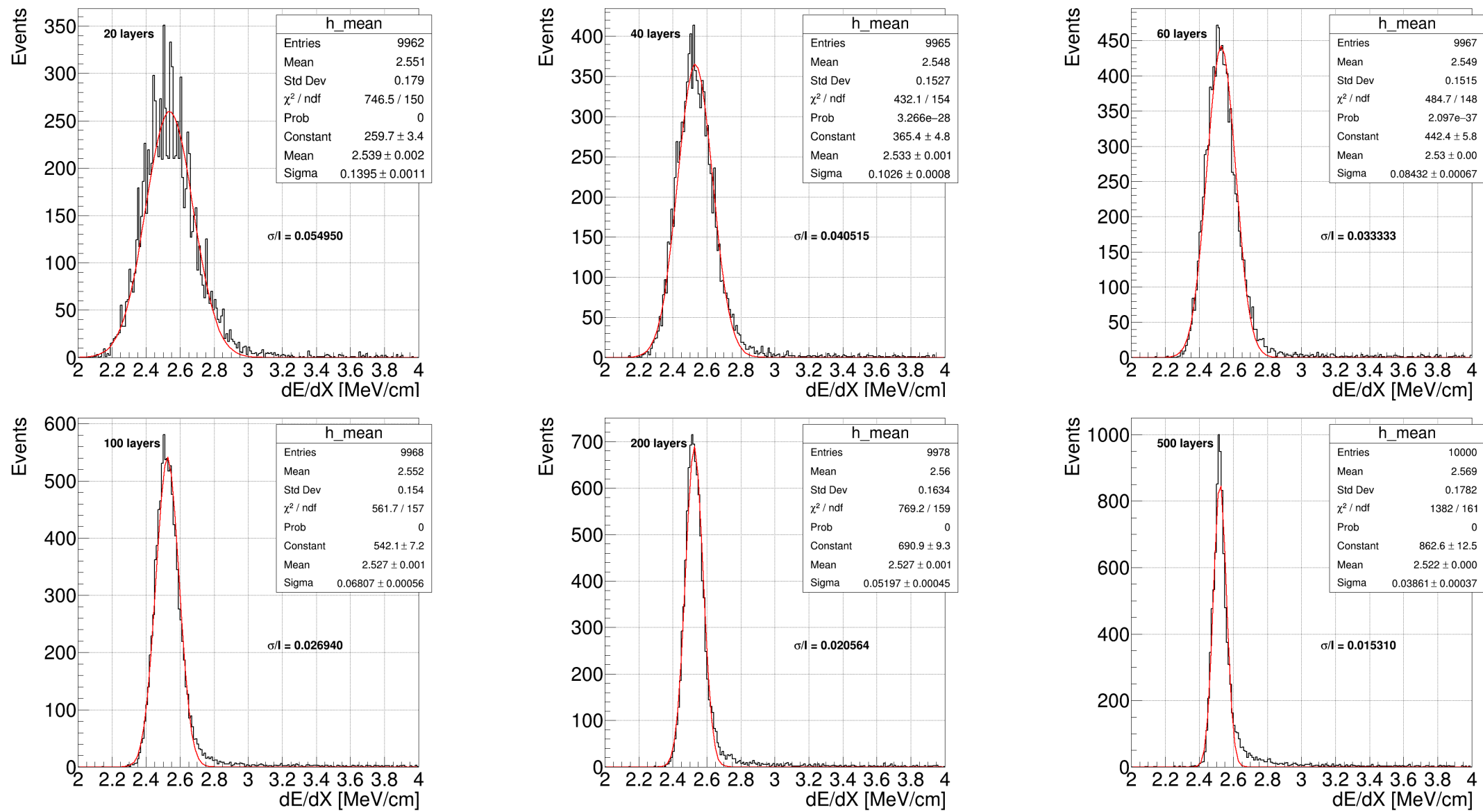


10000 events 穿过100um Si 能量损失分布

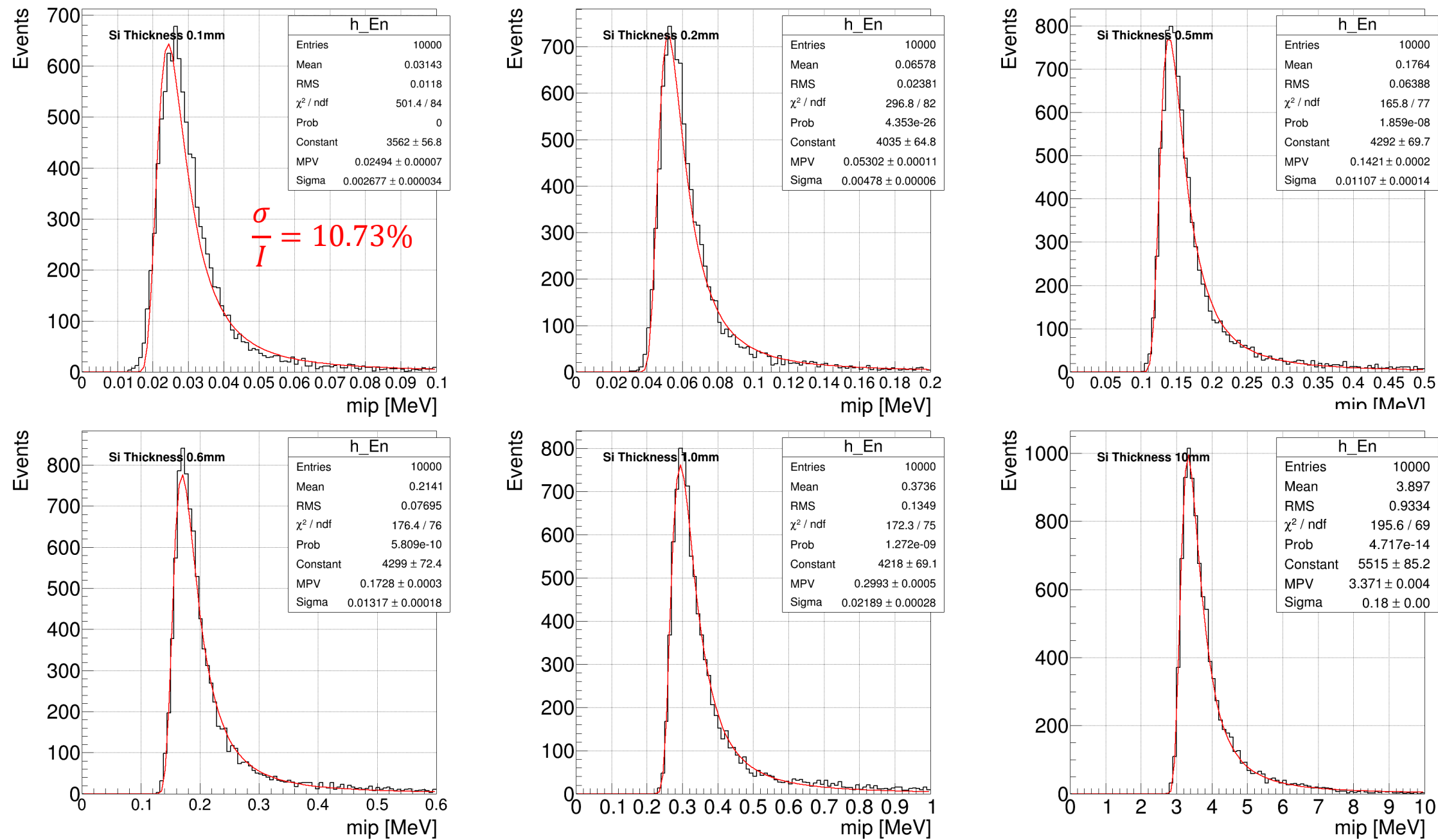


10GeV kaon- 在100umSi 中dE/dX分辨率随
放置层数的分布

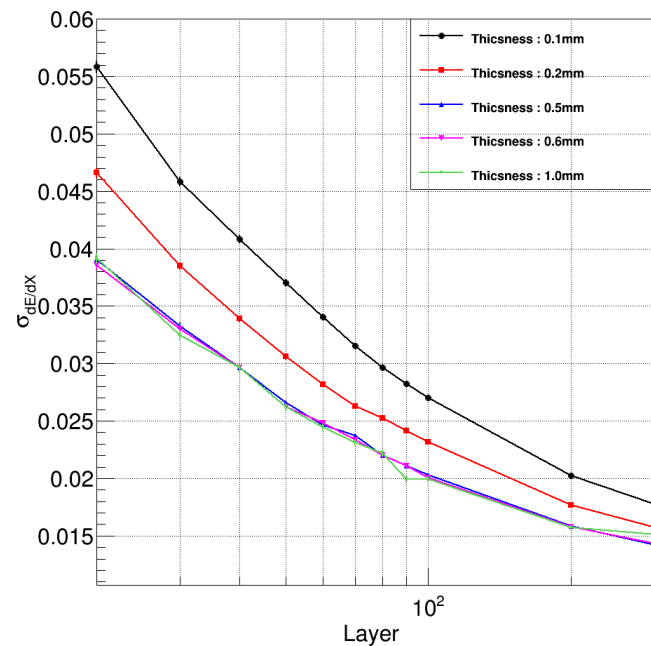
多层Si截断平均拟合结果



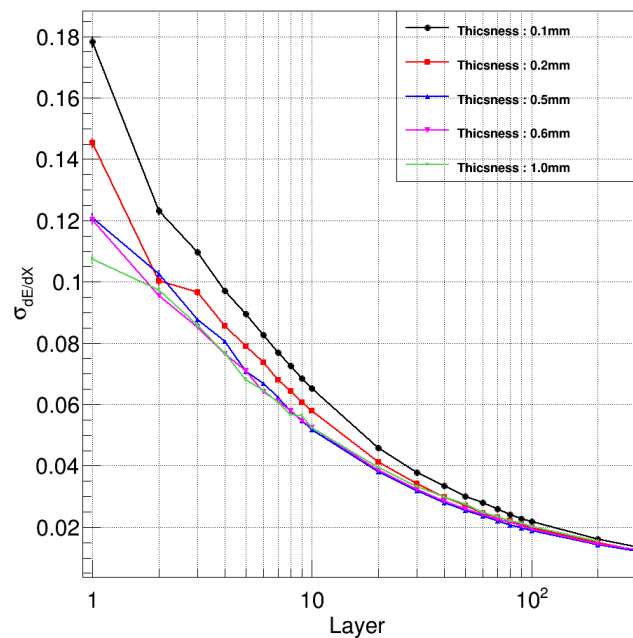
不同厚度单层Si层mip分布



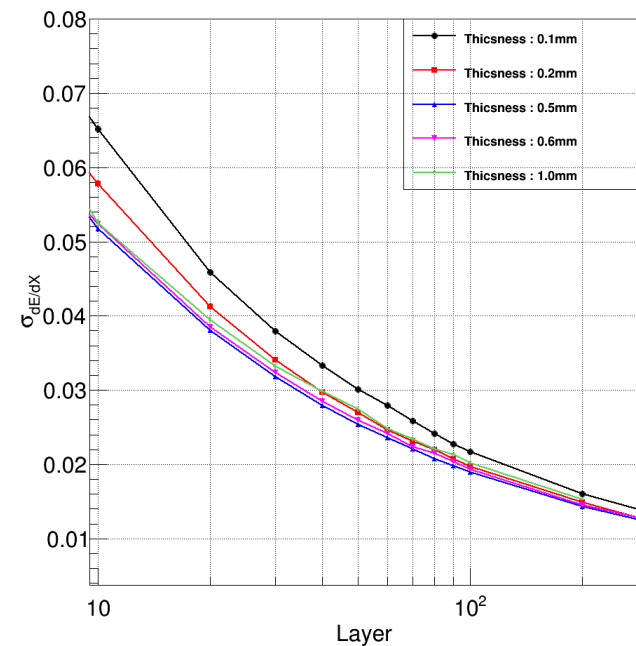
选取两种不同的截断方式结果：60%能量分布截断；1.5mip能量截断



60%能量截断下dE/dX分辨



1.5mip截断下dE/dX分辨



1.5mip截断下dE/dX分辨局部放大